HIGH POWER GaAs FET

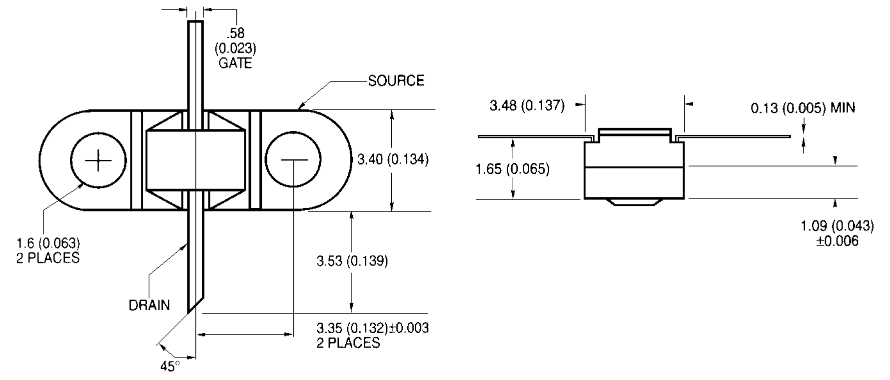
FEATURES INCLUDE:

- High Output Power:
  P1dB = 1.6 W (TYP) @ 12 GHz
- High power gain:
  GLP = 5 dB (TYP) @ 12 GHz
- High power added efficiency:
  Hadd = 18% (TYP) @ 12 GHz

APPLICATIONS:

- **S** to **Ku** Band Power Amplifiers

FET PACKAGE TYPE 30



ELECTRICAL SPECIFICATIONS $T_A = 25\ ^{O}C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
I_{DDS}	SATURATED DRAIN CURRENT $V_{DS} = 3.0$ V $V_{GS} = 0$ V	850	1100	1400	**mA**
$V_{GS\ (off)}$	GATE TO SOURCE CUT-OFF VOLTAGE $V_{DS} = 3.0$ V $I_D = 1.0$ mA	-2	-3	-5	**V**